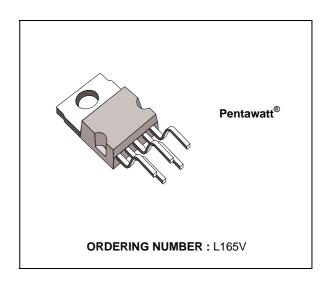


## 3A POWER OPERATIONAL AMPLIFIER

- OUTPUT CURRENT UP TO 3A
- LARGE COMMON-MODE AND DIFFERENTIAL MODE RANGES
- SOA PROTECTION
- THERMAL PROTECTION
- ± 18V SUPPLY

#### **DESCRIPTION**

The L165 is a monolithic integrated circuit in Pentawatt® package, intended for use as power operational amplifier in a wide range of applications, including servo amplifiers and power supplies. The high gain and high output power capability provide superiore performance wherever an operational amplifier/power booster combination is required.



#### **ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
Vs	Supply voltage	± 18	V
V <sub>5</sub> V <sub>4</sub>	Upper power transistor V <sub>CE</sub>	36	V
V <sub>4</sub> V <sub>3</sub>	Lower power transistor V <sub>CE</sub>	36	V
$V_i$	Input voltage	Vs	
$V_{j}$	Differential input voltage	± 15	V
lo	Peak output current (internally limited)	3.5	Α
P <sub>tot</sub>	Power dissipation at T <sub>case</sub> = 90°C	20	W
T <sub>sta</sub> , T <sub>i</sub>	Storage and junction temperature	-40 to 150	°C

#### **APPLICATION CIRCUITS**

Figure 1. Gain > 10.

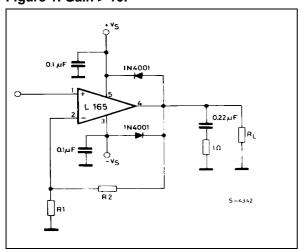
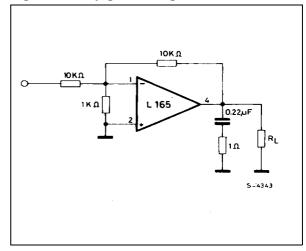
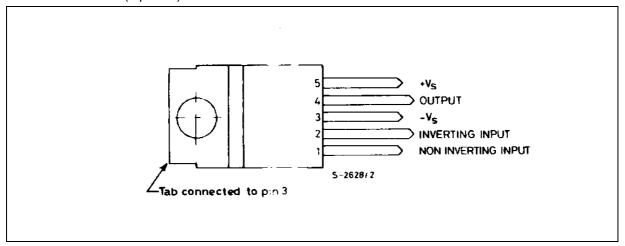


Figure 2. Unity gain configuration.

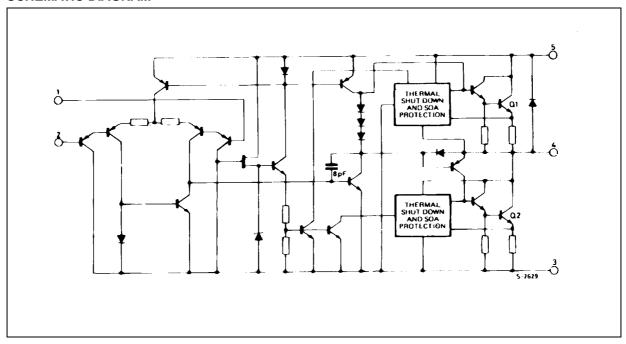


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### PIN CONNECTION (top view)



### **SCHEMATIC DIAGRAM**



### **THERMAL DATA**

Symbol	Parameter	Value	Unit
R <sub>th-j-case</sub>	Thermal resistance junction-case max	3	°C/W

# **ELECTRICAL CHARACTERISTICS** (Vs = $\pm$ 15 V, T<sub>j</sub> = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Unit	
$V_s$	Supply Voltage			± 6		± 18	>	
I <sub>d</sub>	Quiescent Drain Current				40	60	mA	
$I_b$	Input Bias Current	V <sub>s</sub> = ± 18 V				0.2	1	μΑ
$V_{os}$	Input Offset Voltage					± 2	± 10	mV
I <sub>os</sub>	Input Offset Current					± 20	± 200	nA
SR	Slew-rate	G <sub>v</sub> = 10	G <sub>v</sub> = 10			8		V/μs
		G <sub>v</sub> = 1 (°)				6		ν/μ5
Vo	Output Voltage Swing	f = 1 kHz			27 24		$V_{pp}$	
		f = 10 kHz		= 0.3 A = 3 A		27 23		$V_{PP}$
R	Input Resistance (pin 1)	_ f = 1 KHz		100	500		ΚΩ	
$G_v$	Voltage Gain (open loop)				80		dB	
e <sub>N</sub>	Input Noise Voltage	B = 10 to 10 000 Hz			2		μV	
i <sub>N</sub>	Input Noise Current	D = 10 to 10 00	B = 10 to 10 000 HZ			100		pA
CMR	Common-mode Rejection	$R_g \leq 10 \text{ K}\Omega$	G۷	= 30 dB		70		dB
SVR	Supply Voltage Rejection	$ \begin{array}{c} R_g = 22 \ \text{K}\Omega \\ V_{ripple} = 0.5 \ V_{rms} \\ f_{ripple} = 100 \ \text{Hz} \end{array} \qquad \begin{array}{c} G_v = 10 \\ \text{dB } G_v = 100 \end{array} $		G <sub>v</sub> = 10		60	dB	dB
				dB G <sub>v</sub> = 100		40		dB
	Efficiency				70		%	
				I <sub>p</sub> = 3 A; P <sub>o</sub> = 18 W		60		%
T <sub>sd</sub>	Thermal Shut-down Case	P <sub>tot</sub> = 12 W			110		- °C	
	Temperature	P <sub>tot</sub> = 6 W				130		

Figure 3. Open loop frequency response.

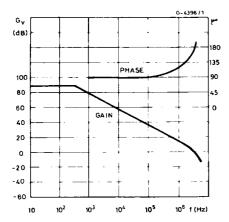


Figure 5. Large signal frequency response.

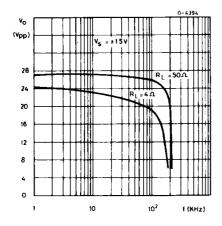


Figure 7. Safe operating area and collector characteristics of the protected power transistor.

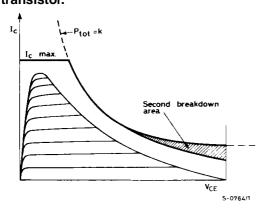


Figure 4. Closed loop frequency response (circuit of figure 2).

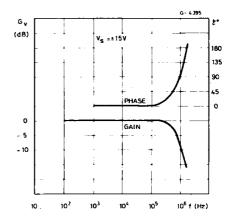


Figure 6. Maximum output current vs. voltage [VCE] across each output transistor.

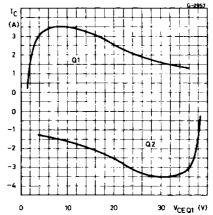
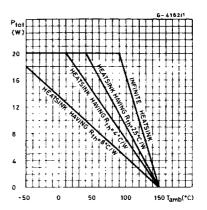


Figure 8. Maximum allowable power dissipation vs. ambient temperature.



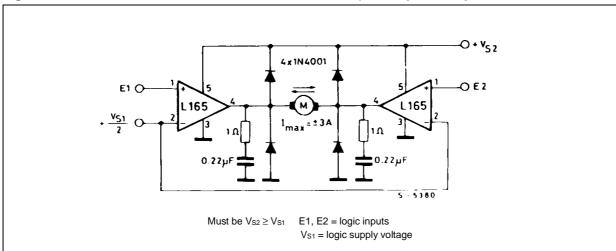


Figure 9. Bidirectional DC motor control with TTL/CMOS/ $\mu$ P compatible inputs.



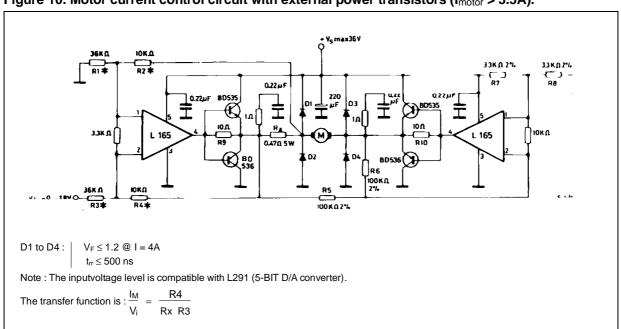


Figure 11. High current tracking regulator.

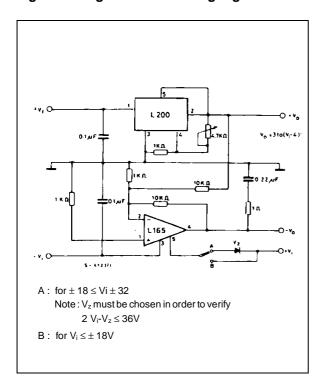


Figure 12. Bidirectional speed control of DC motor (Compensation networks not shown).

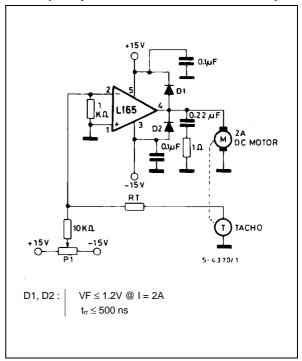
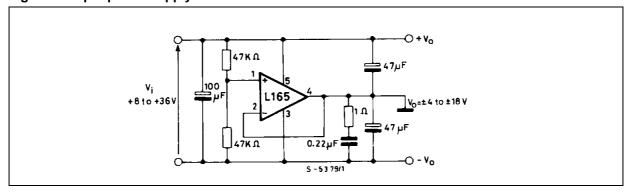


Figure 13. Split power supply.



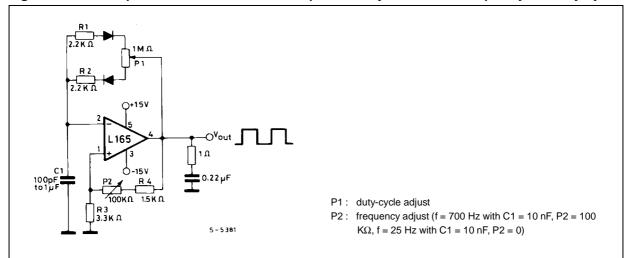
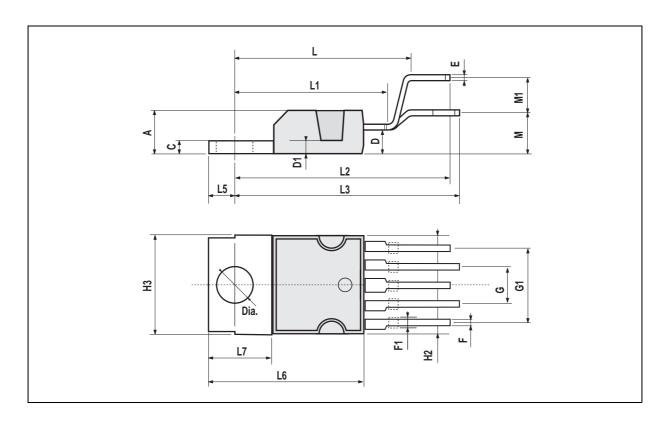


Figure 14. Power squarewave oscillator with independent adjustments for frequency and duty-cycle.

### PENTAWATT PACKAGE MECHANICAL DATA

DIM.	mm			inch			
DIN.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
Α			4.8			0.189	
С			1.37			0.054	
D	2.4		2.8	0.094		0.110	
D1	1.2		1.35	0.047		0.053	
Е	0.35		0.55	0.014		0.022	
F	0.8		1.05	0.031		0.041	
F1	1		1.4	0.039		0.055	
G		3.4		0.126	0.134	0.142	
G1		6.8		0.260	0.268	0.276	
H2			10.4			0.409	
H3	10.05		10.4	0.396		0.409	
L		17.85			0.703		
L1		15.75			0.620		
L2		21.4			0.843		
L3		22.5			0.886		
L5	2.6		3	0.102		0.118	
L6	15.1		15.8	0.594		0.622	
L7	6		6.6	0.236		0.260	
М		4.5			0.177		
M1		4			0.157		
Dia	3.65		3.85	0.144		0.152	



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